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MANIPAL INSTITUTE OF TECHNOLOGY  
Manipal University



**SEVENTH SEMESTER B.TECH (E & C) DEGREE END SEMESTER  
EXAMINATION - NOV/DEC 2016  
SUBJECT: LOW POWER VLSI DESIGN (ECE - 429)**

**TIME: 3 HOURS**

**MAX. MARKS: 50**

**Instructions to candidates**

- Answer **ANY FIVE** full questions.
- Missing data may be suitably assumed.

- 1A. Derive an expression for short circuit power in CMOS inverter and discuss the significance of the expression from the point of view of opportunity for reduction of power.
- 1B. Discuss DVS and AVS techniques for reducing dynamic power dissipation in VLSI. (5+5)
- 2A. Explain i) Segmented Bus architecture and ii) Low swing Bus employed in VLSI to reduce dynamic power.
- 2B. Describe i) Guarded Evaluation and ii) pre-computation techniques employed in low power designs. Also, using appropriate VHDL coding show how they can be implemented at the RTL level. (5+5)
- 3A. Using appropriate example show how Bus invert coding technique can be implemented. What are its salient features? Illustrate with examples.
- 3B. Estimate the intrinsic wire delay of a Cu wire of length 10mm in 0.13  $\mu\text{m}$  CMOS technology, with a thickness 0.3  $\mu\text{m}$ , width 0.3  $\mu\text{m}$  and height 0.35  $\mu\text{m}$  above M1 ground plane with  $\text{SiO}_2$  dielectric. Assume: resistivity = 24  $\text{ohm-}\mu\text{m}$ ,  $c = 0.12 \text{ fF}/\mu\text{m}$ . What will be the delay if a buffer with 150ps delay is inserted at the centre of the line?. What is the overall delay if the line is divided into 4 segments and buffers of 150ps are inserted? (5+3+2)
- 3C. What are the techniques used to reduce cross talk in interconnects? List.
- 4A. Explain i) Dual  $V_{th}$  technique and ii) Dynamic body biasing technique for reducing the leakage power in VLSI circuit and compare them
- 4B. Discuss the process level techniques for reducing leakage power in MOSFETs. (5+5)

- 5A. Describe the concept of i) Gate-length Biasing and ii) LECTOR for leakage reduction
- 5B. Discuss the techniques employed for Gate Leakage control in MOSFETs
- 5C. Assume that the Display in your cell phone has an average transition delay ( shut down and wake up) of 5ms, power in sleeping and working state are 5mW and 60 mW respectively. Also the transition energy is of 40 mW-sec. What is the minimum idle time required to consider switching to power down mode?
- (5+3+2)
- 6A. Discuss the DPM policies with their salient features
- 6B. What are the techniques used while coding to reduce power in processors? Explain with examples.
- (5+5)